ABSTRACT (FIG. 3)

"NONVOLATILE SEMICONDUCTOR MEMORY DEVICE AND METHOD OF MANUFACTURING THE SAME"

According to one embodiment, a nonvolatile semiconductor memory device includes an element region, a gate insulating film, a first gate electrode, an intergate insulating film, a second gate electrode and an element isolation region. The gate insulating film is formed on the element region. The first gate electrode is formed on the gate insulating film. The intergate insulating film is formed on the first gate electrode and has an opening. The second gate electrode is formed on the intergate insulating film and in contact with the first gate electrode via the opening. The element isolation region encloses a laminated structure formed by the element region, the gate insulating film, and the first gate electrode. The air gap is formed between the element isolation region and side surfaces of the element region, the gate insulating film and the first gate electrode.

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